

Abstract of the Disclosure:

A single crystal SiC layer is formed on a substrate surface by heating the substrate under existence of a raw material containing C or C and Si. SiC is deposited on the single crystal SiC layer by the vapor phase growth method or the liquid phase growth method. In the step of forming the single crystal SiC layer, the raw material is supplied in the vicinity of the surface, and the raw material in the vicinity of the surface is given a partial pressure higher at least by a predetermined rate than that of an impurity. Thus, the impurity is prevented from reaching the surface, so that the surface is prevented from being etched by the impurity.

20250570-011802